



# He irradiation of HEA at HAL

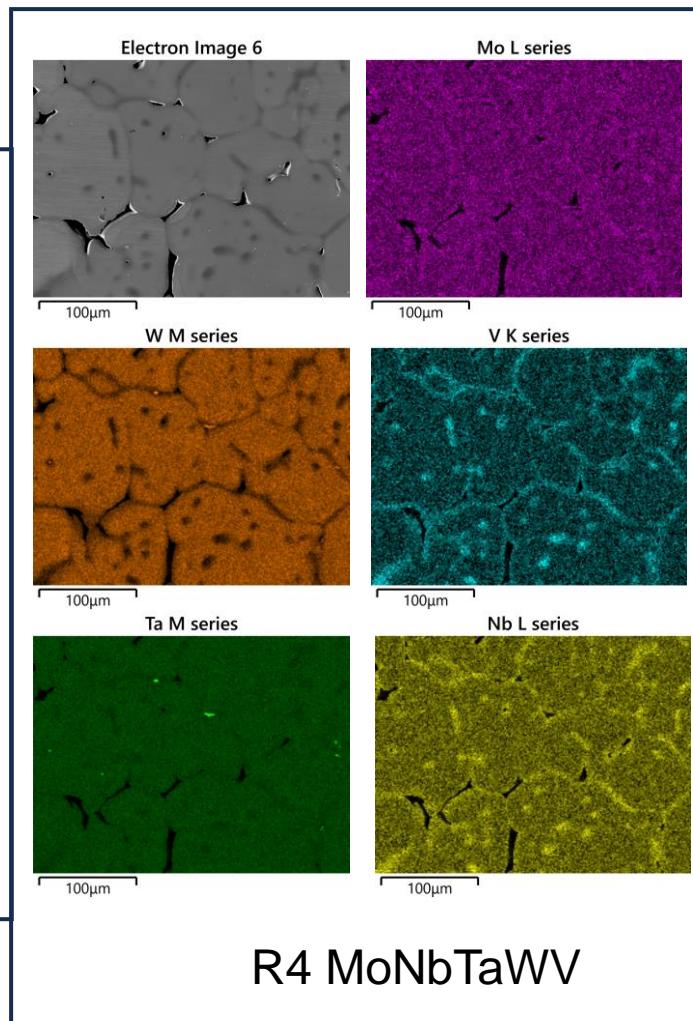
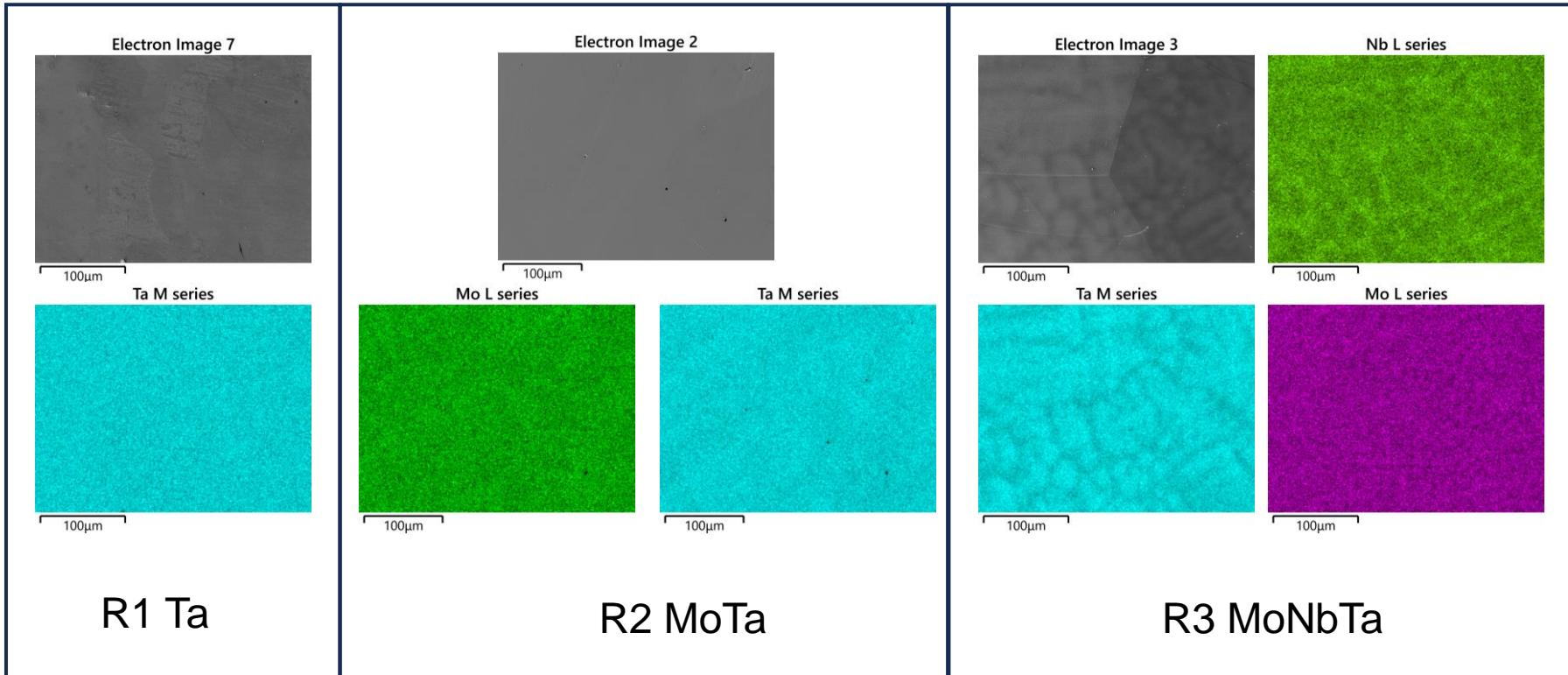
**Zhehao Chen**

13.06.2024



## 1. He in Ta series RHEA

Samples: Arc-melted Ta(R1), MoTa(R2), MoNbTa(R3), MoNbTaWV(R4)

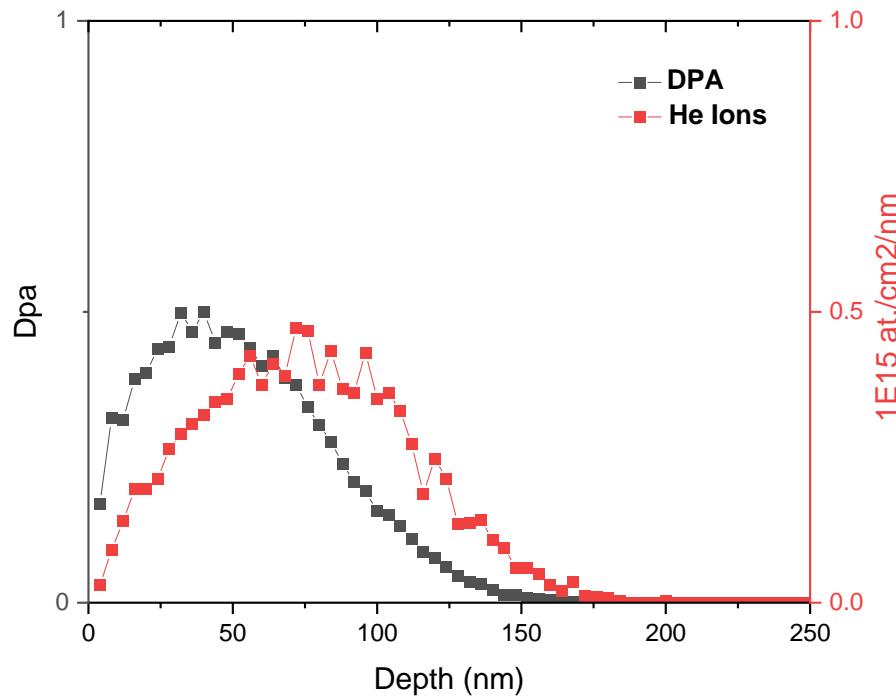


# 1. He in Ta series RHEA

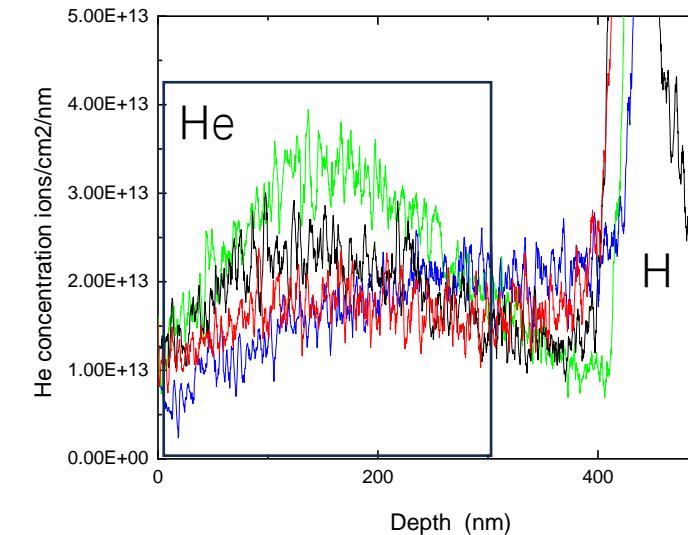
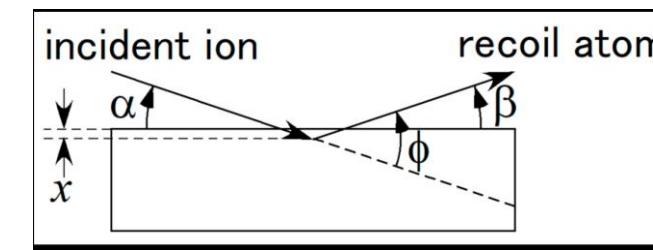


Irradiation: 5E16 25 keV He (ions/cm<sup>2</sup>) , room temperature

ERDA and TEM characterization of He concentration after annealing at RT - 1473k for 1h



SRIM simulation of 25 keV He in Ta

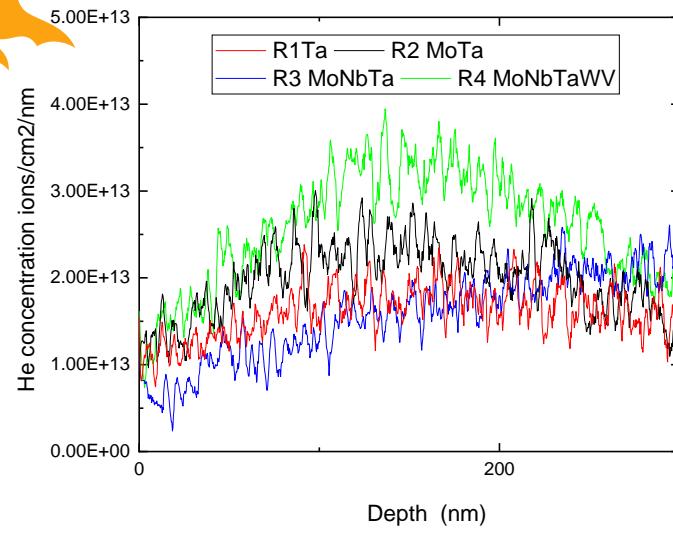


ERDA principle and a example spectrum

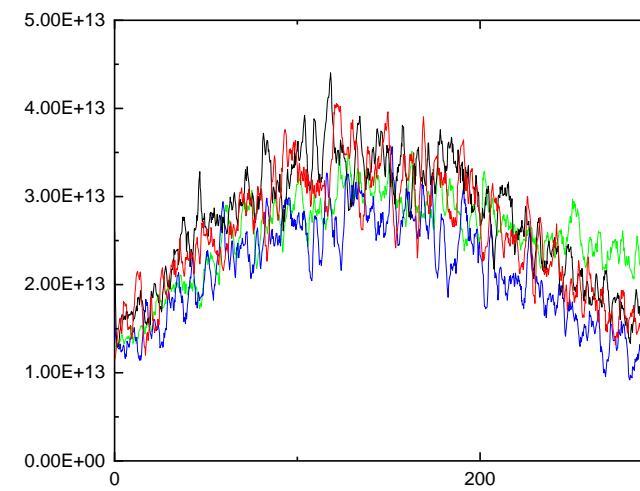
# 1. He in Ta series RHEA



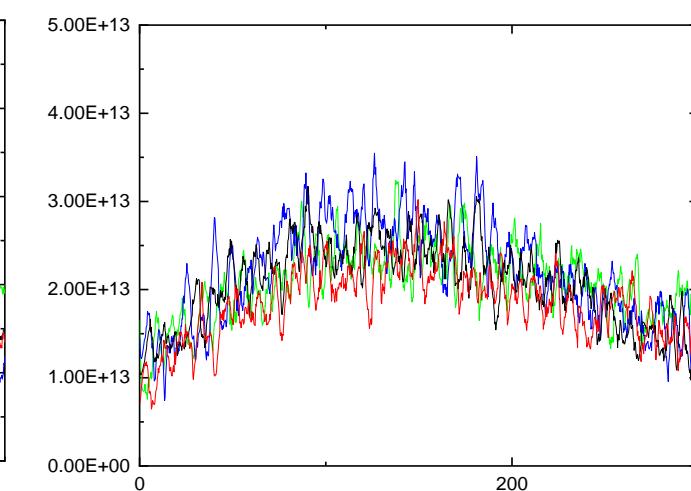
ERDA measurements of helium depth distribution after annealing at RT - 1073k for 1h



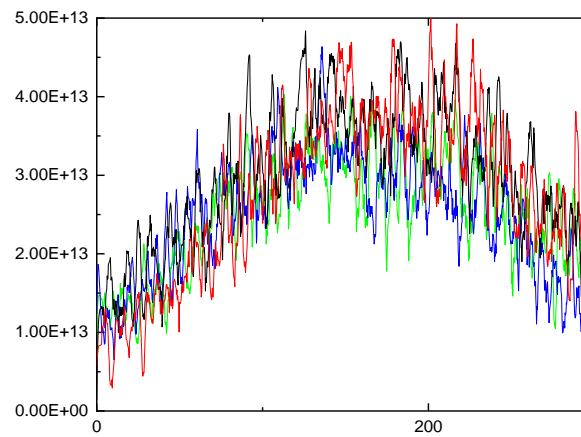
RT



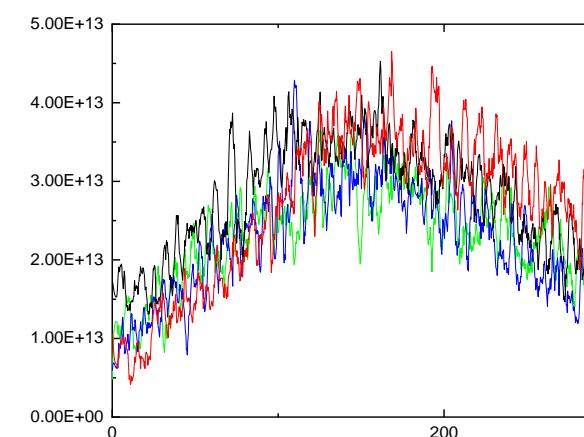
473 K



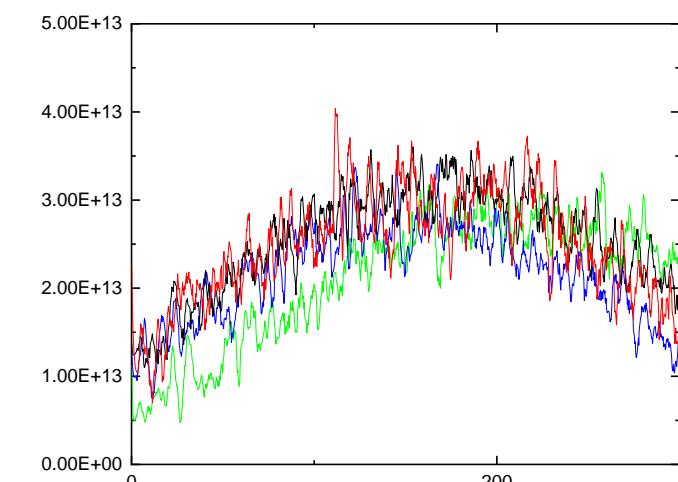
673 K



873 K



1073 K

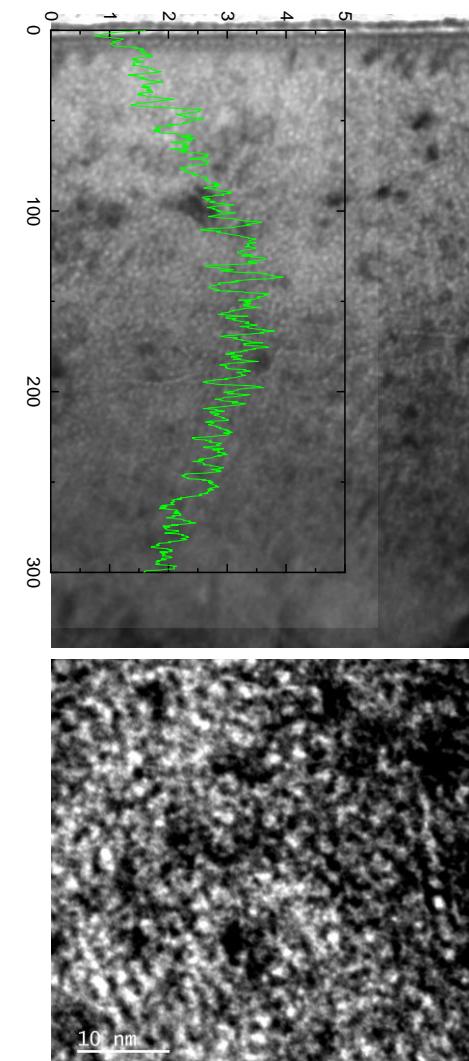
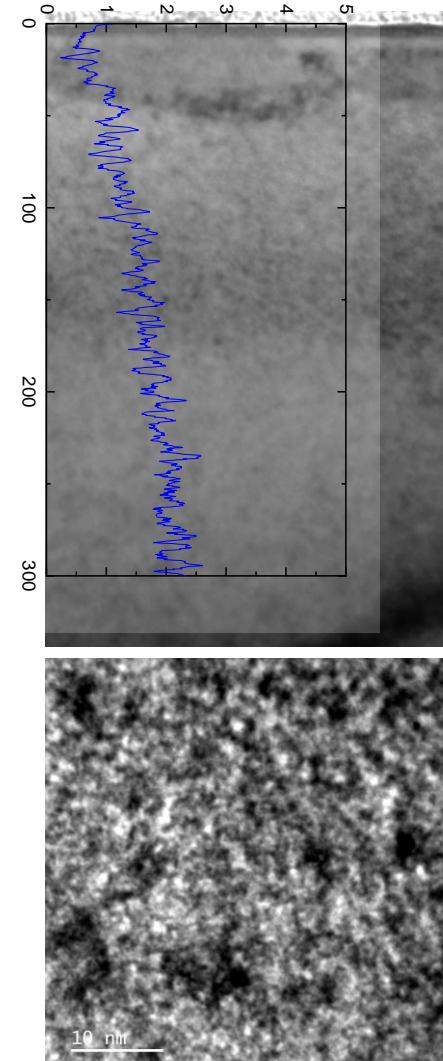
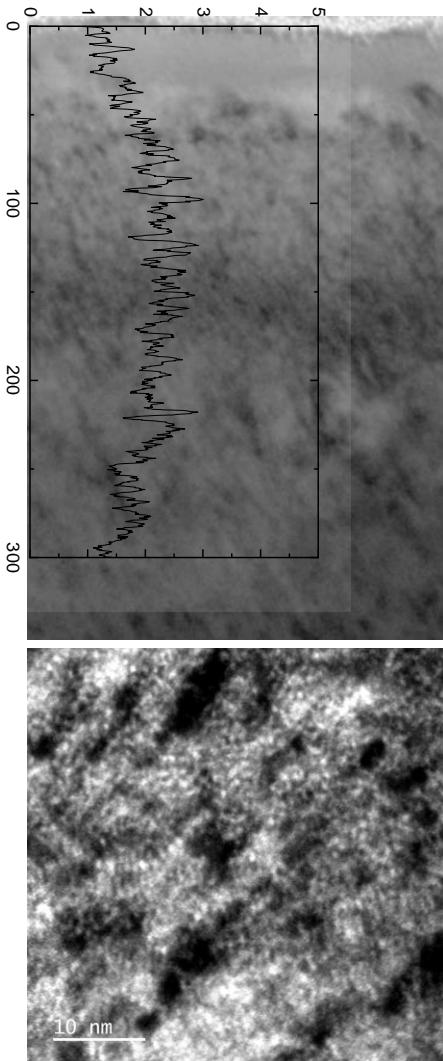
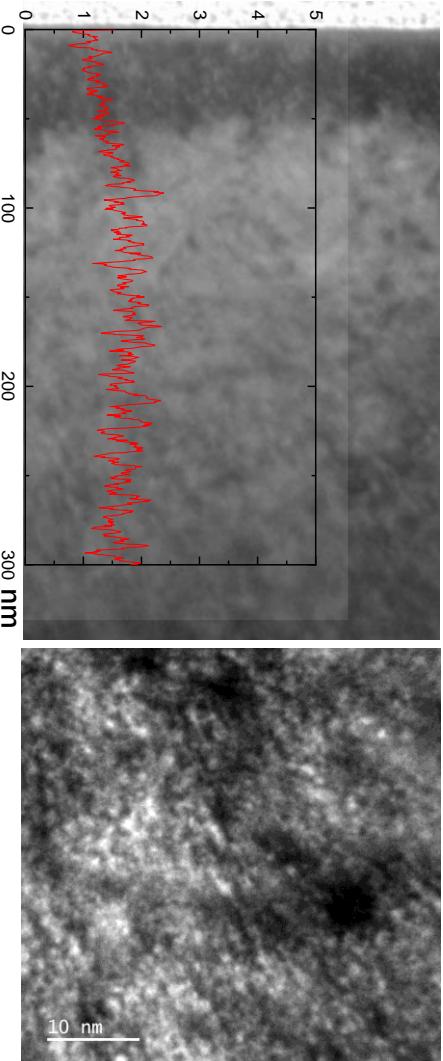
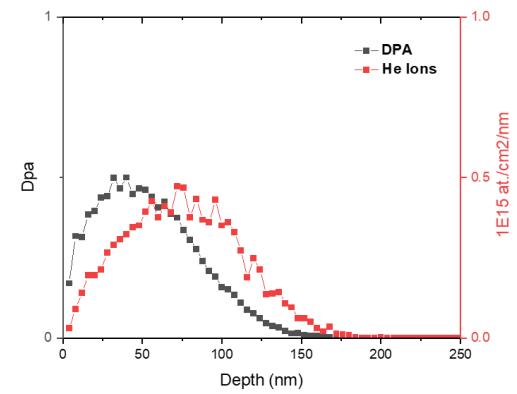


1273 K

# 1. He in Ta series RHEA

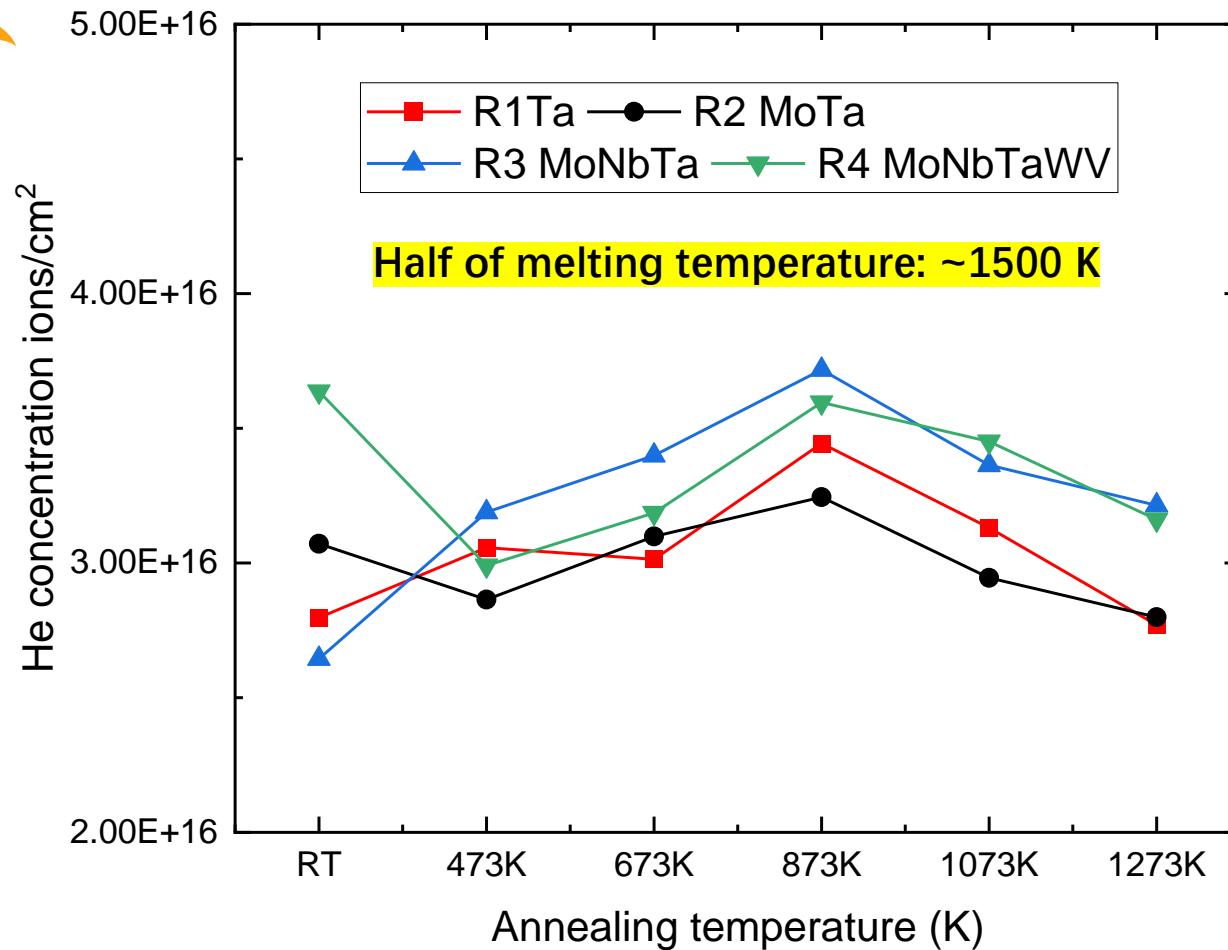


He concentration  $\times 10^{13}$  ions/nm/cm<sup>2</sup>



TEM BF image of He cavities depth distribution

## 1. He in Ta series RHEA



- MoNbTaWV has a larger helium concentration after RT implantation.
- The helium concentration increases until the temperature reaches 873K, after which it decreases.
- Apparently, R1, R2 have fast decreasing rate than R3, R4. Higher annealing temperatures is needed to observe a clear tendency.

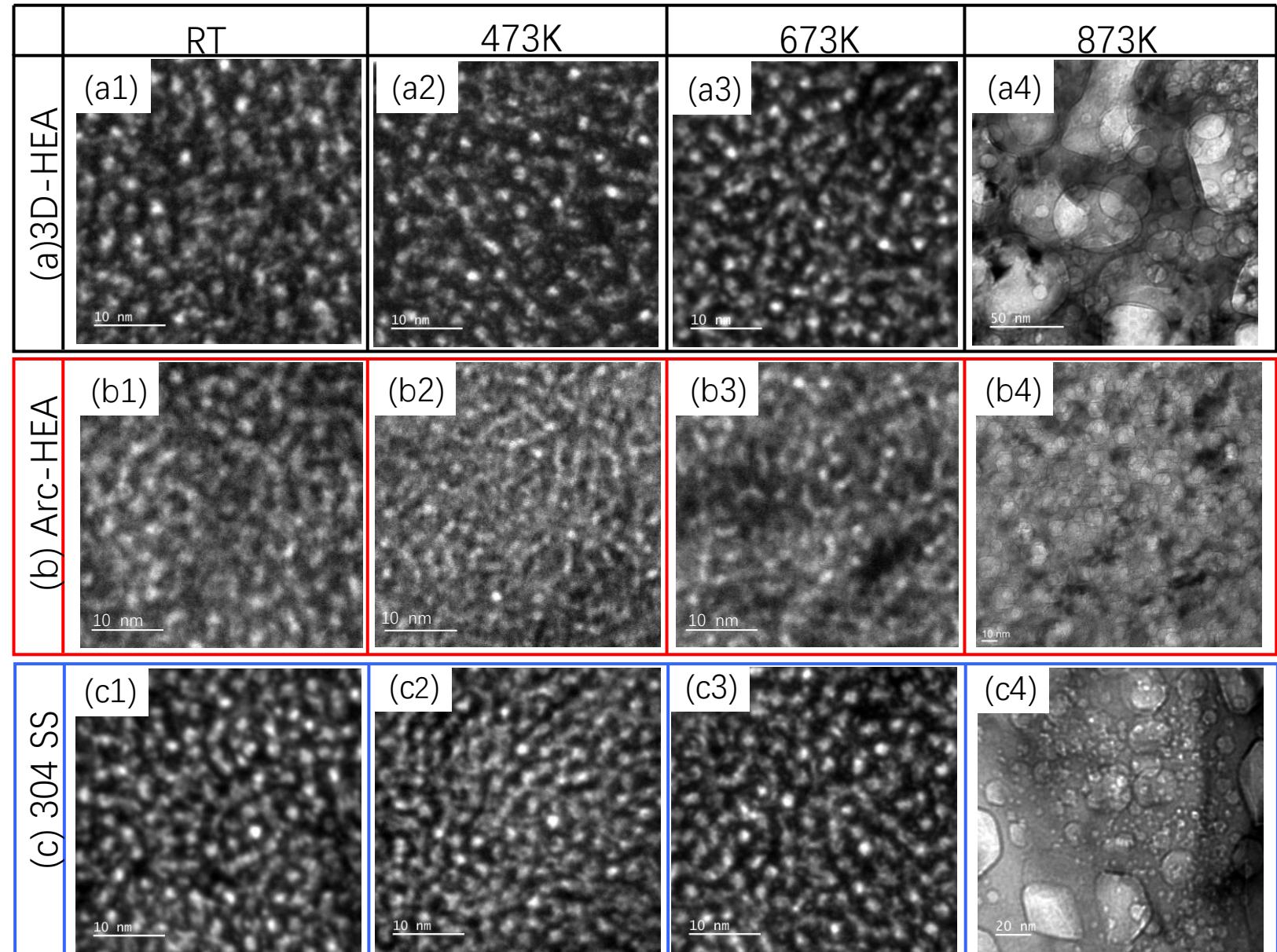
ERDA measurement of total He concentration from 0-300nm depth after annealing

## Discussion: Comparison with FCC HEA



Samples: Arc-melted and 3D printed Cantor HEAs (FeMnCrCoNi), 304 steel as reference. FCC, large crystal (around 100  $\mu\text{m}$ )

Irradiation: 1E16 3 MeV Ni and 5E17 500 keV He (ions/ $\text{cm}^2$ ) , room temperature

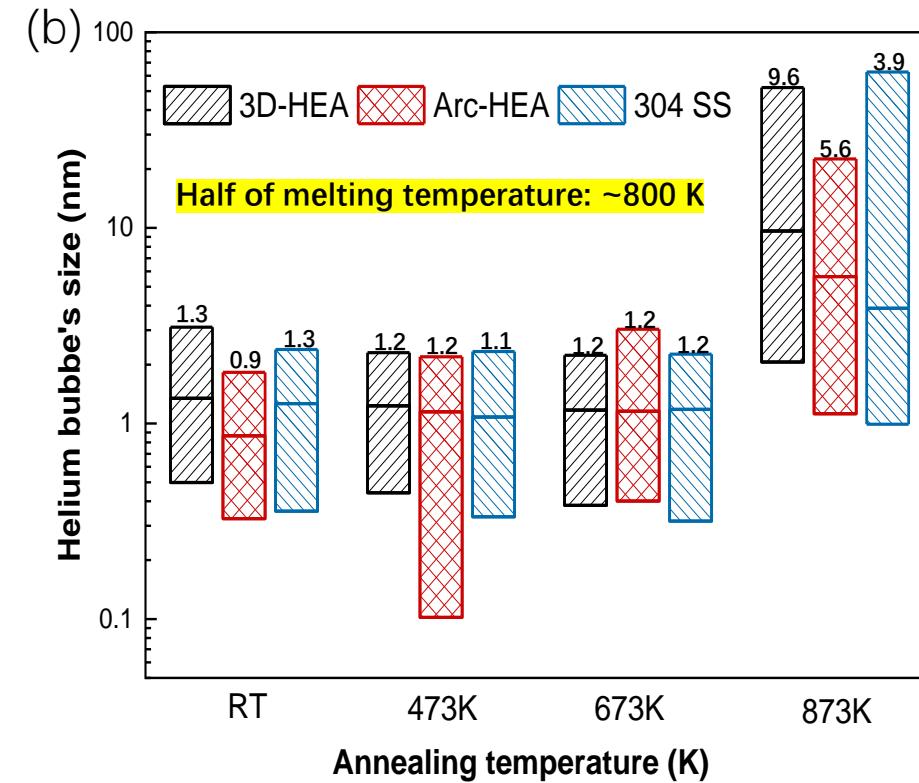
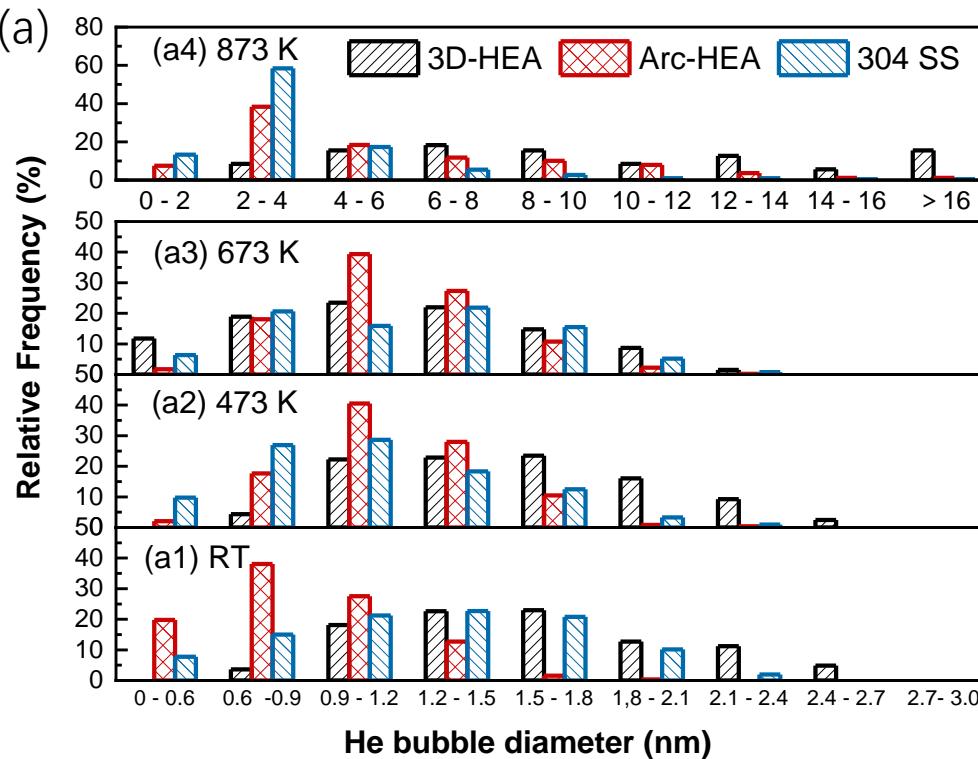


Annealing after irradiation RT – 873 K, 1h

7/14

zhehao.chen@helsinki.fi

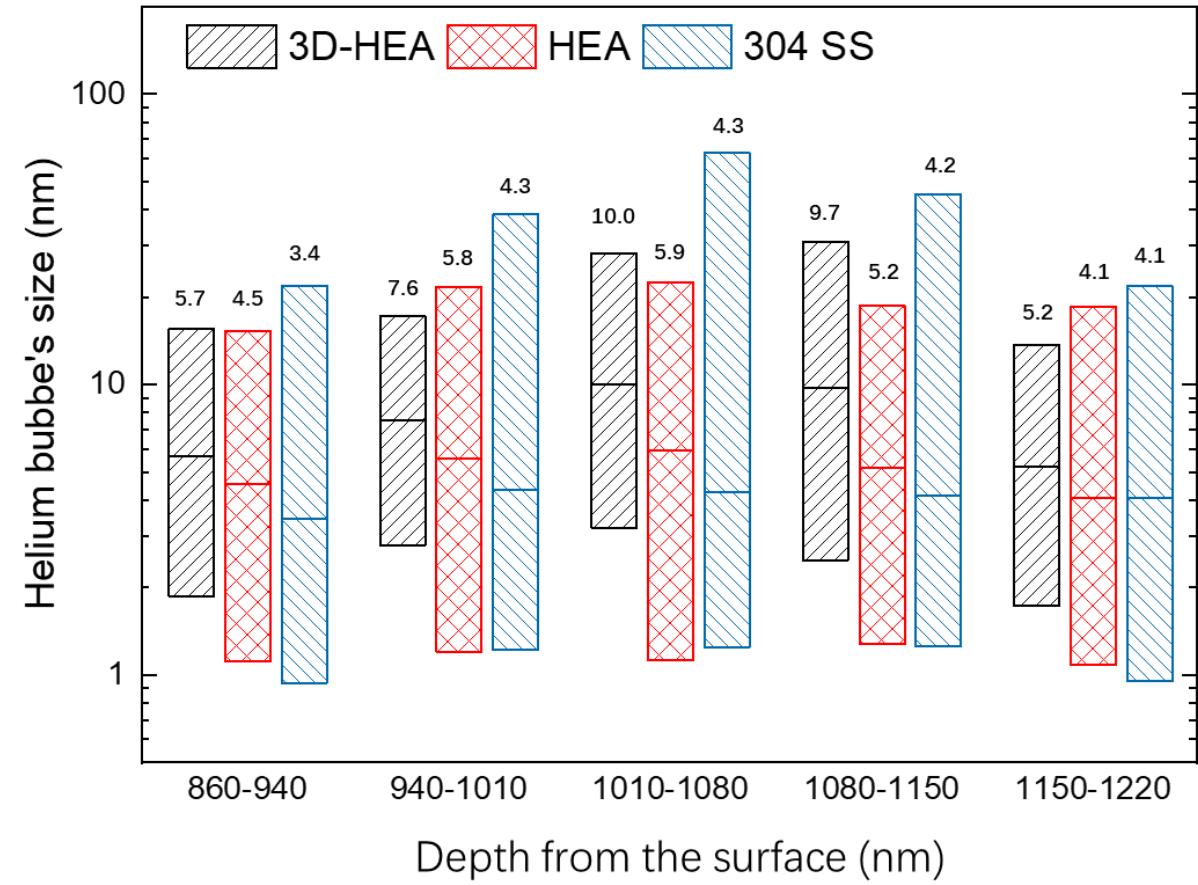
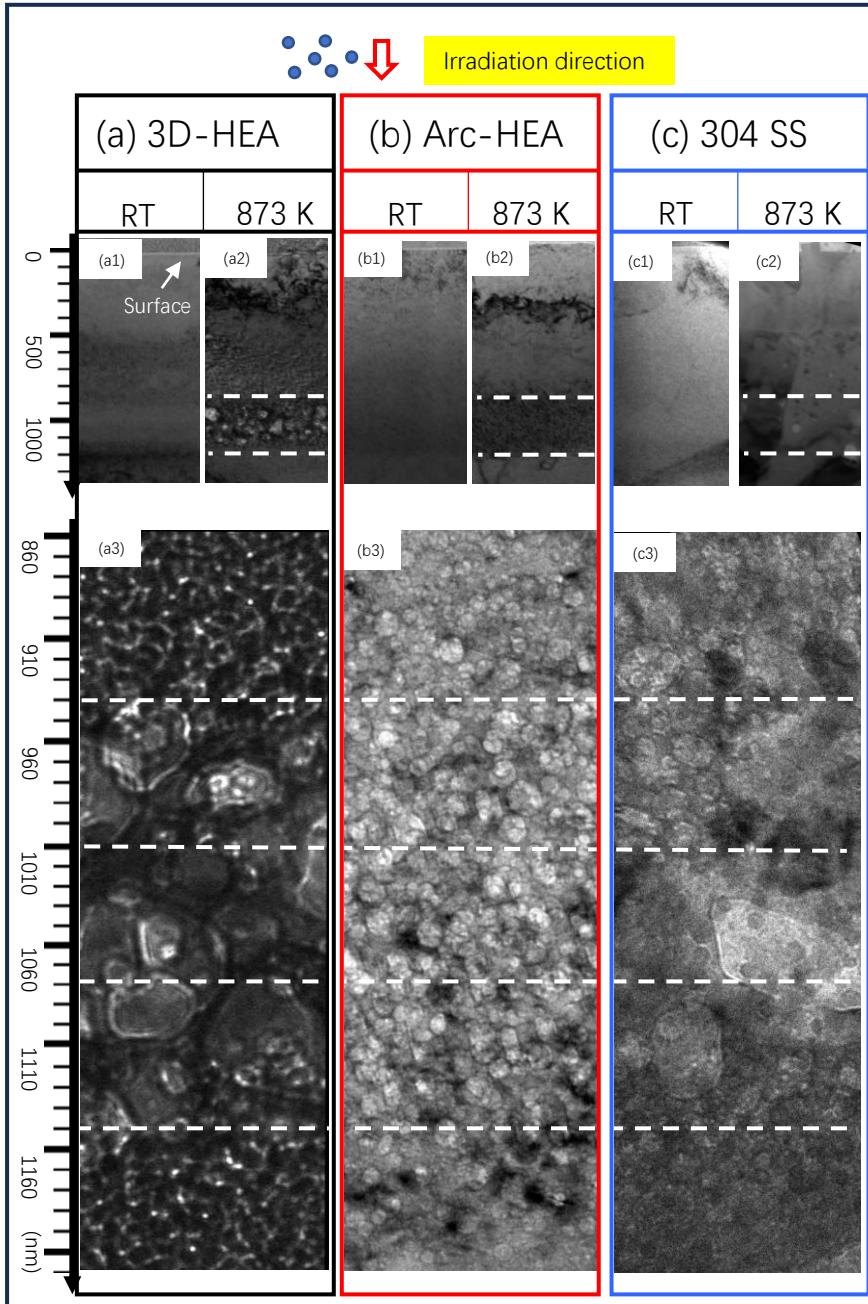
## Discussion: Comparison with FCC HEA



Size distributions (a) and average sizes (b) of He cavities



# Depth profile after 873k annealing



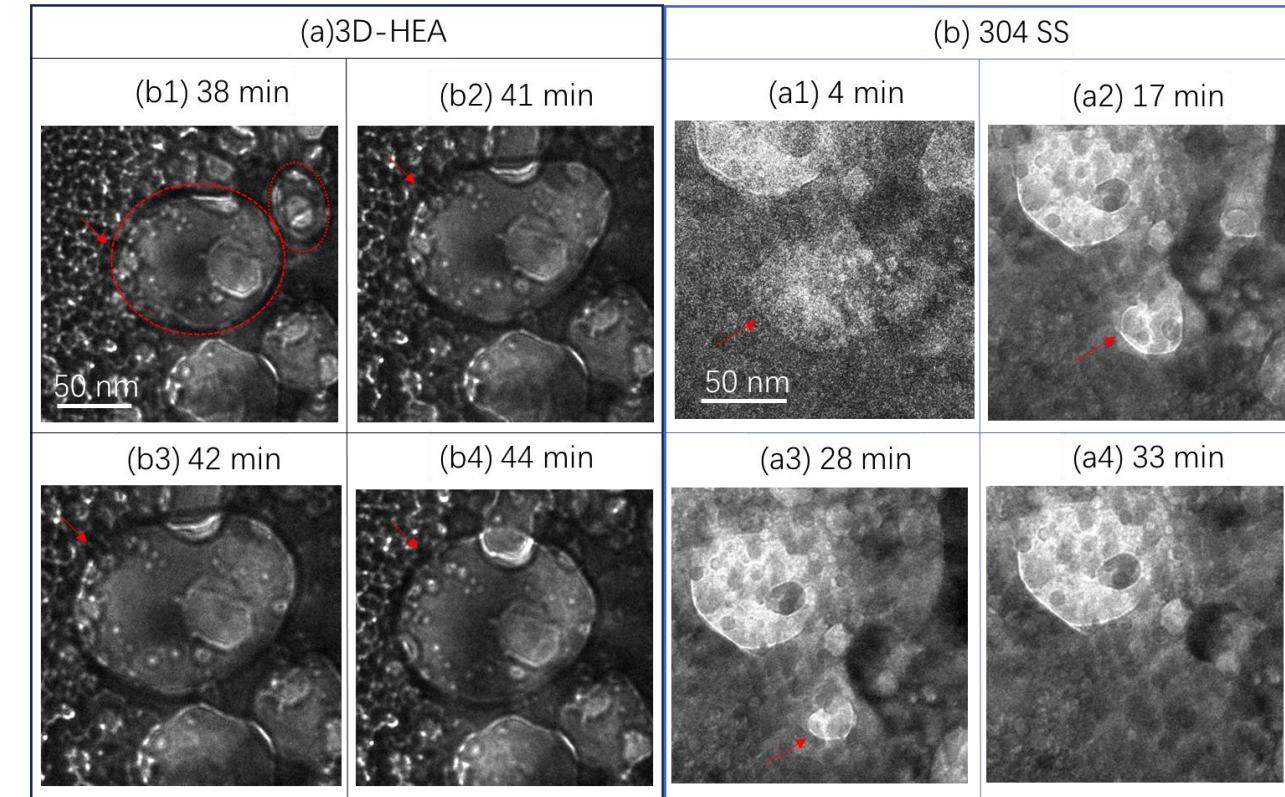
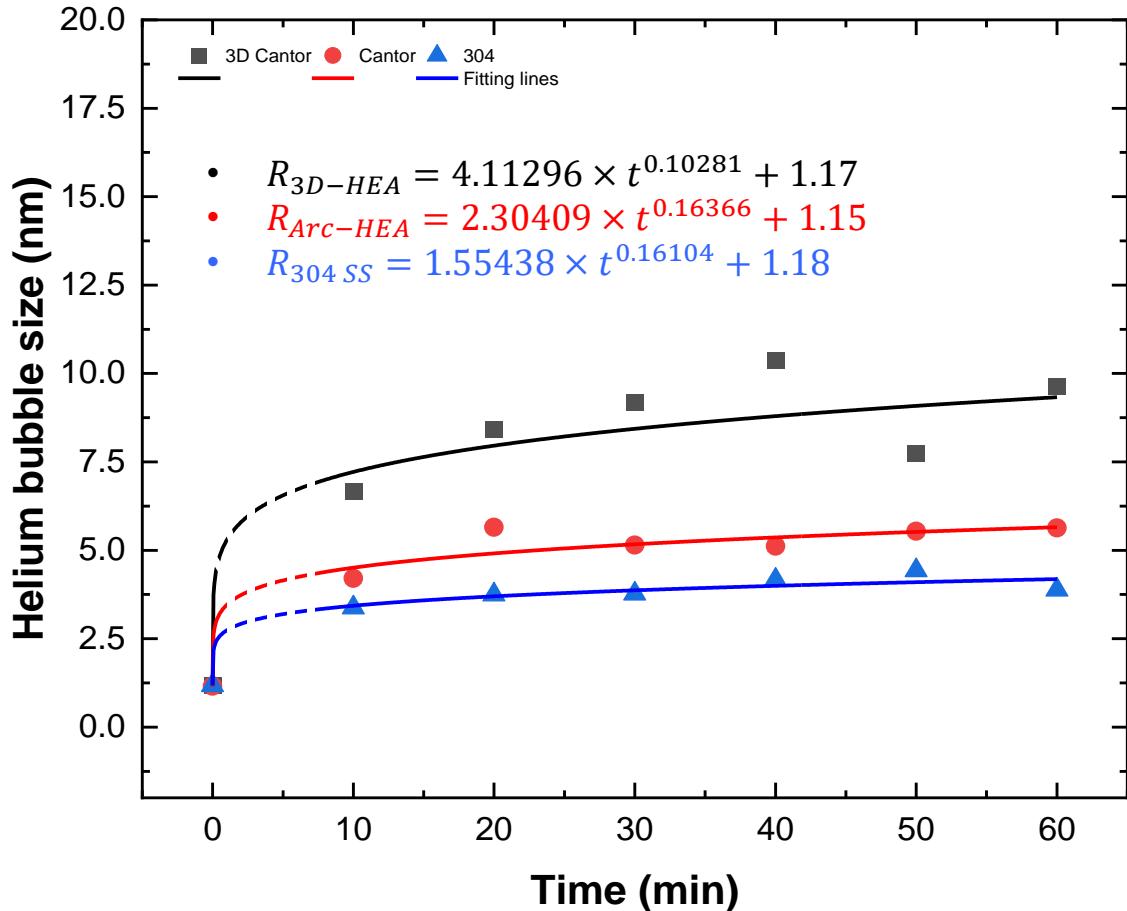
Top: He bubble size distributions and depth profiles in 3D-HEA, Arc-HEA and 304 SS. Each bar shows maximum, average and minimum value, and the average value is indicated on the top.

Left : TEM BF image: 3D-HEA (a), Arc-HEA (b) and 304 SS (c) as-irradiated and after sequential 873K annealing. Each of the damage areas is divided into 5 blocks as show in (a3-c3).



## Discussion: Comparison with FCC HEA

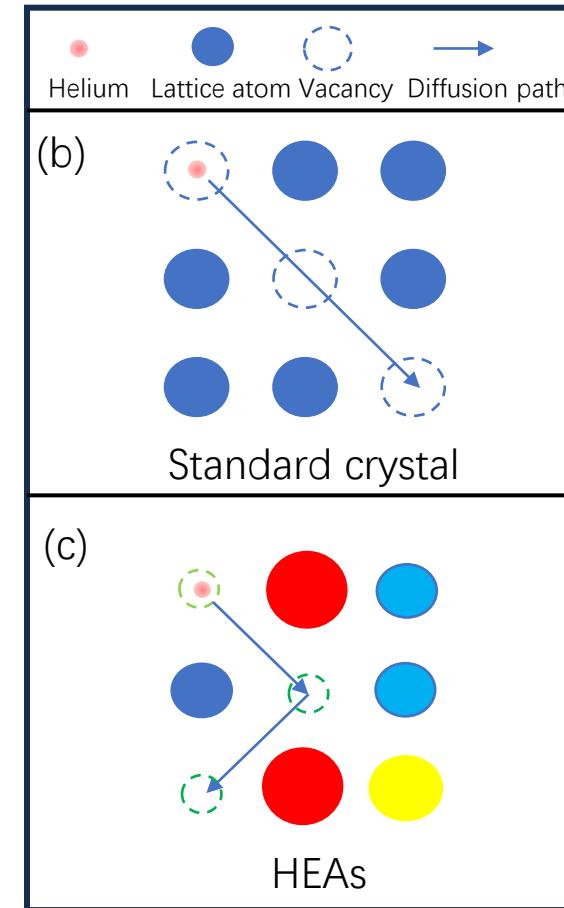
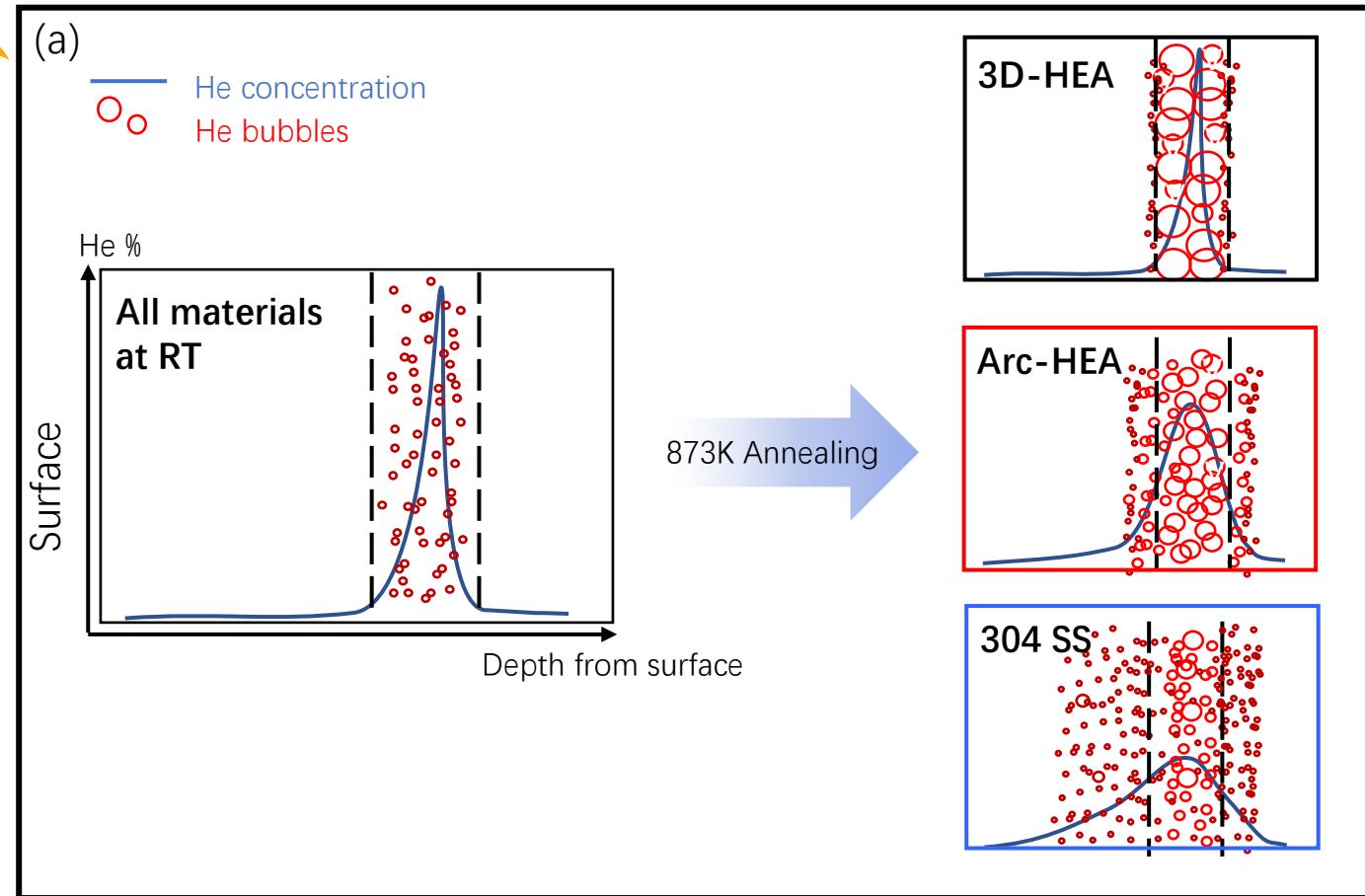
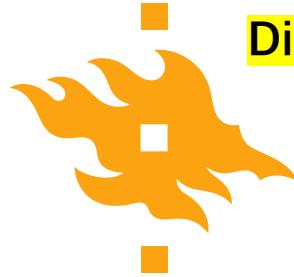
### In-situ TEM and annealing at 873k, 1h



Left: Average He bubbles size as a function of annealing time during in-situ annealing of 3D-HEA, Arc-HEA and 304 SS. The empirical formula from Ref. [1] is fitted to the data for reference.

Right: TEM BF images illustrating two He bubble growth processes: (a) the coalescence process as observed in 3D-HEA, and (b) Ostwald Ripening (OR) as observed in 304 SS

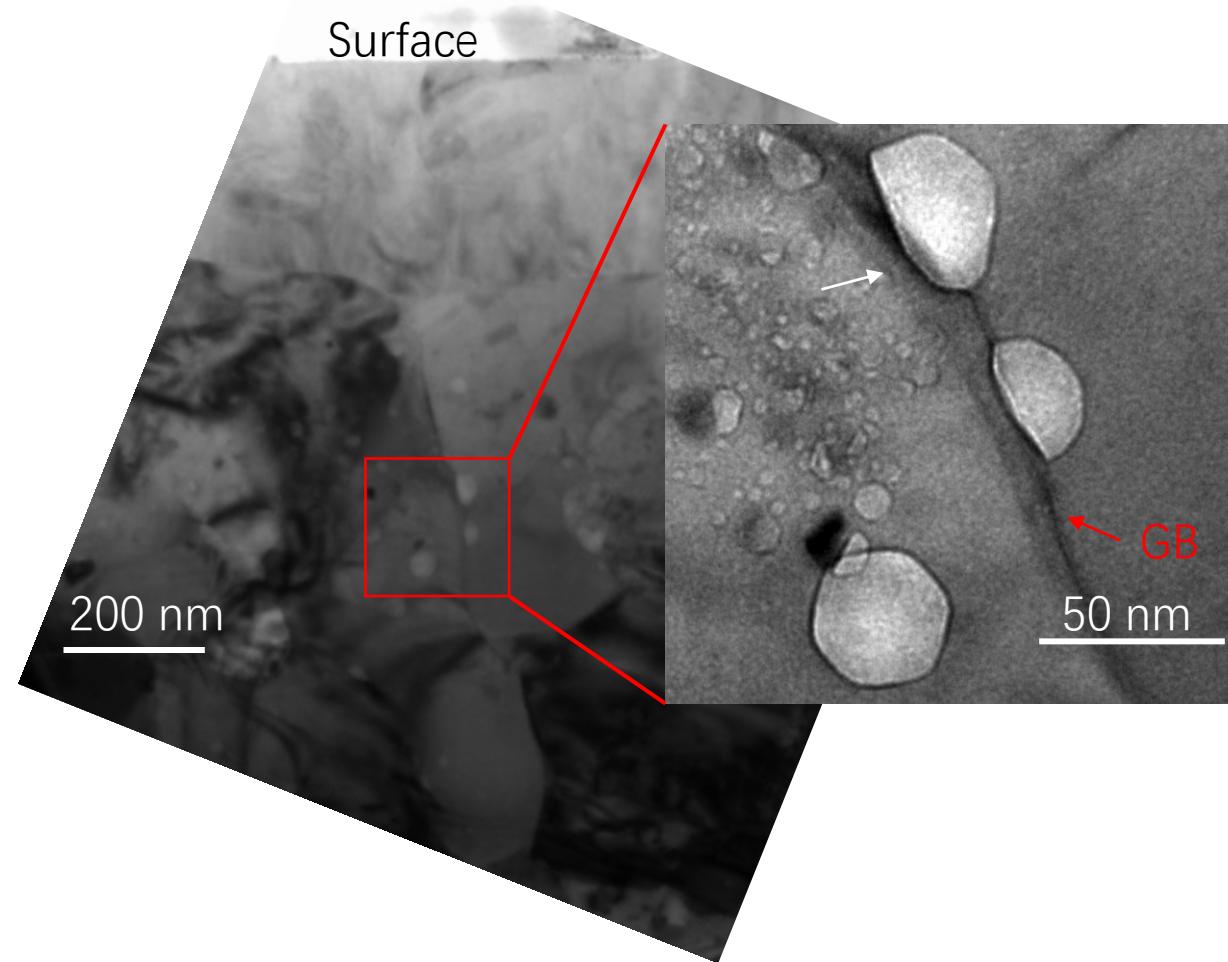
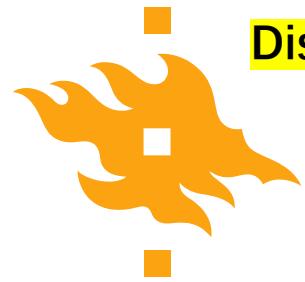
## Discussion: Comparison with FCC HEA



Sketch of He diffusion in FCC HEA

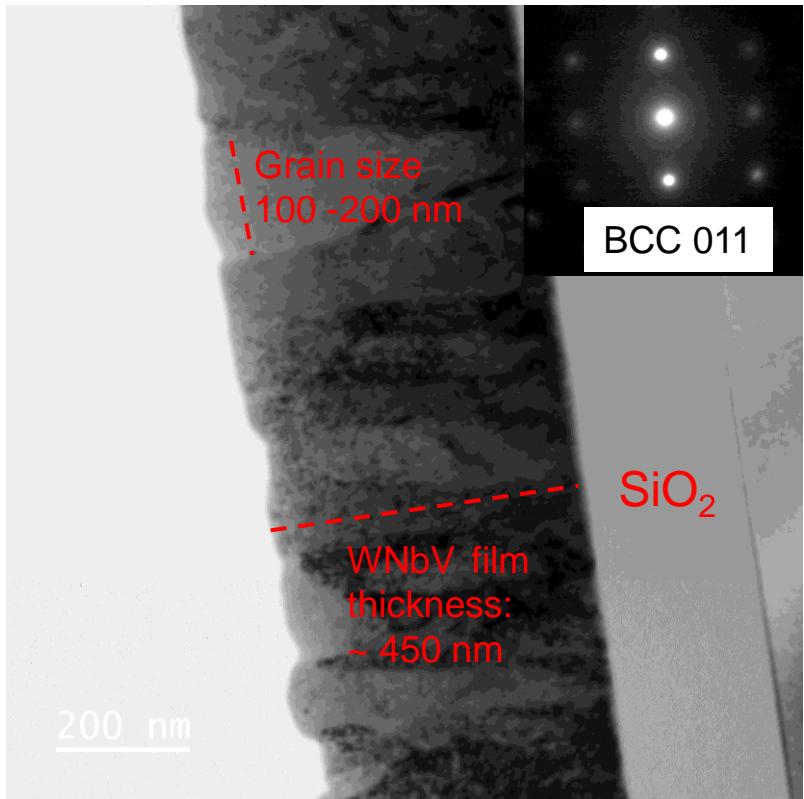
- In inhomogeneous implantation, the size of helium cavities depends on the local helium concentration.
- Sluggish diffusion leads to high local helium concentrations, resulting in larger cavities.
- Sluggish diffusion may be related to **random diffusion paths** in HEA, which affected by the **diversity of migration energie**

## Discussion: Comparison with FCC HEA

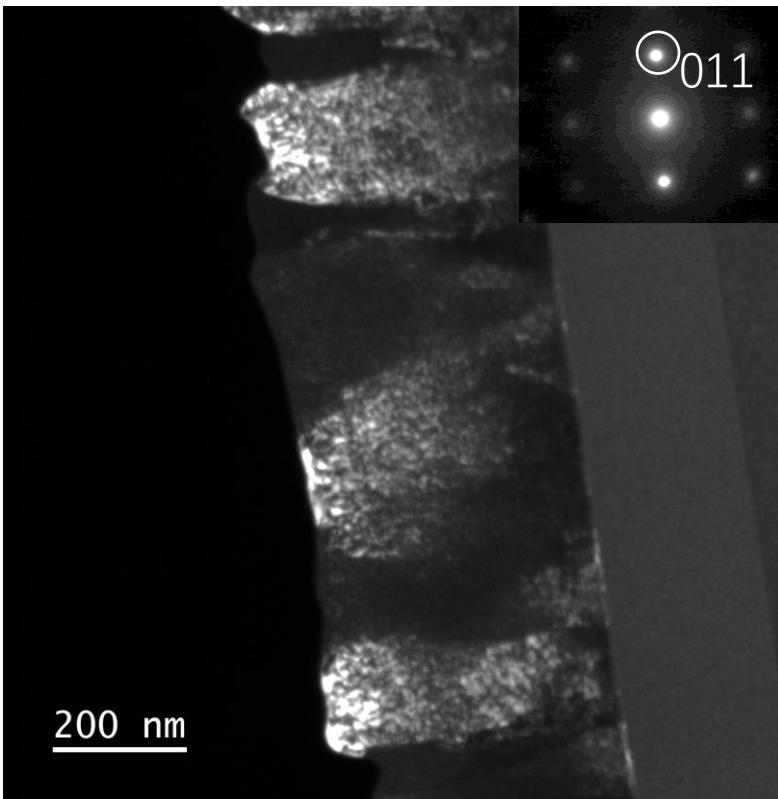


Long-range diffusion lead to helium cavities growing at grain boundary in 304 SS.

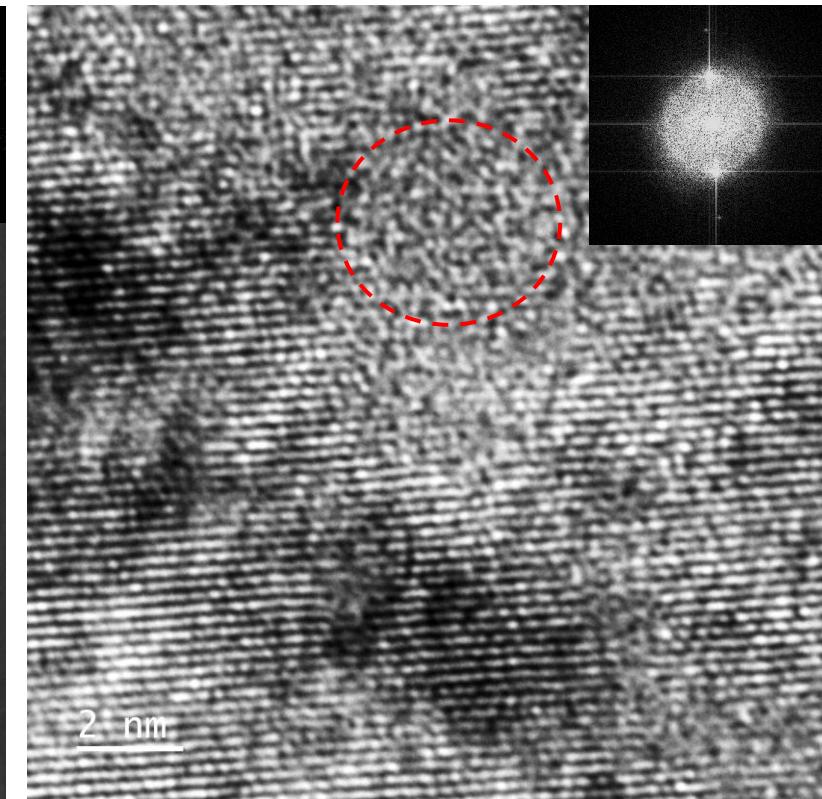
## 2. RHEA thin film synthesis: WNbV



Cross-sectional TEM BF image



Cross-sectional TEM DF image



HRTEM image

- The WNbV thin film with a primary BCC matrix was successfully synthesized (by Spyros) using magnetron sputtering.
- It contains many amorphous domains. High-temperature annealing is needed to homogenize the crystal structure and increase the grain size.



Next step:

1. Fixing the high temperature oven!
2. Annealing up to 1600 K and TEM characterization
3. WV thin film samples?

**Thank you for your attention!**